

EasyPIM™ module with fast Trench/Fieldstop IGBT3 and emitter controlled 3 diode and PressFIT / NTC

Features

- Electrical features
 - $V_{CES} = 650\text{ V}$
 - $I_{C\text{ nom}} = 50\text{ A} / I_{CRM} = 100\text{ A}$
 - Trench IGBT 3
 - Low switching losses
- Mechanical features
 - Al_2O_3 substrate with low thermal resistance
 - Compact design
 - PressFIT contact technology
 - Rugged mounting due to integrated mounting clamps



Typical appearance

Potential applications

- Air conditioning

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

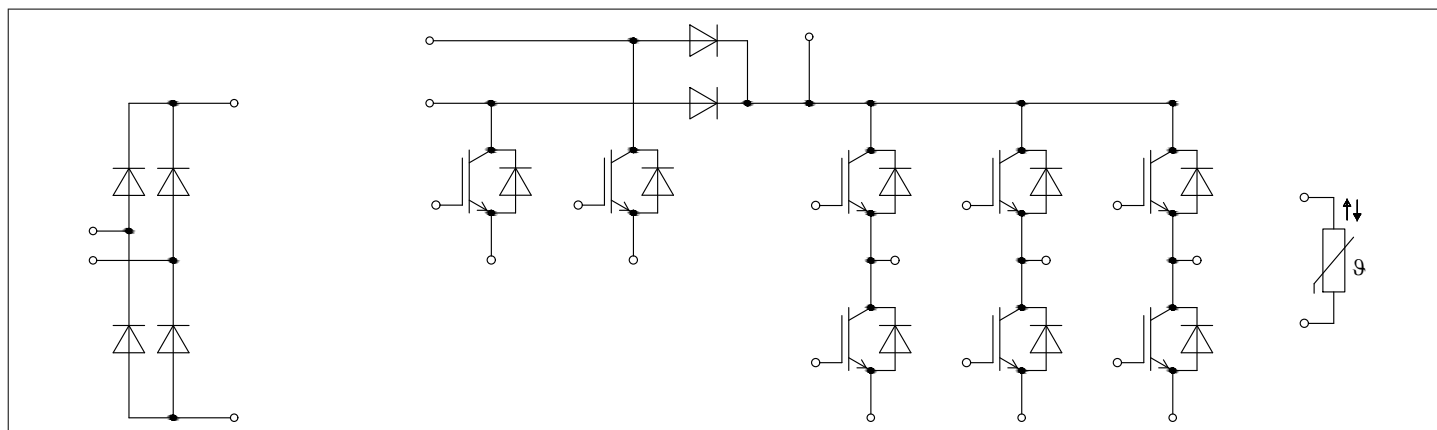


Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	IGBT, Inverter	3
3	Diode, Inverter	5
4	Diode, Rectifier	6
5	IGBT, Boost	6
6	Diode, Boost	8
7	Diode, Reverse	9
8	NTC-Thermistor	9
9	Characteristics diagrams	10
10	Circuit diagram	19
11	Package outlines	20
12	Module label code	21
	Revision history	22
	Disclaimer	23

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50 \text{ Hz}$, $t = 1 \text{ min}$	2.5	kV
Internal isolation		basic insulation (class 1, IEC 61140)	Al_2O_3	
Creepage distance	d_{Creep}	terminal to heatsink	11.5	mm
Creepage distance	d_{Creep}	terminal to terminal	6.3	mm
Clearance	d_{Clear}	terminal to heatsink	10.0	mm
Clearance	d_{Clear}	terminal to terminal	5.0	mm
Comparative tracking index	CTI		>200	
Relative thermal index (electrical)	RTI	housing	140	°C

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			30		nH
Module lead resistance, terminals - chip	$R_{AA'+CC'}$	$T_H = 25^\circ\text{C}$, per switch		6		mΩ
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_H = 25^\circ\text{C}$, per switch		5		mΩ
Storage temperature	T_{stg}		-40		125	°C
Mounting force per clamp	F		40		80	N
Weight	G			39		g

Note: The current under continuous operation is limited to 25 A rms per connector pin.

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{vj} = 25^\circ\text{C}$	650	V
Implemented collector current	I_{CN}			50	A
Continuous DC collector current	I_{CDC}	$T_{vj \max} = 175^\circ\text{C}$	$T_H = 65^\circ\text{C}$	45	A
Repetitive peak collector current	I_{CRM}	$t_P = 1 \text{ ms}$		100	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 50\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.45	1.90	V
			$T_{vj} = 125\ ^\circ C$		1.60		
			$T_{vj} = 150\ ^\circ C$		1.70		
Gate threshold voltage	V_{GEth}	$I_C = 0.8\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		5.05	5.80	6.45	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 400\ V$			0.5		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			0		Ω
Input capacitance	C_{ies}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			3.1		nF
Reverse transfer capacitance	C_{res}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.095		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 650\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.018	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 50\ A, V_{CE} = 300\ V, V_{GE} = \pm 15\ V, R_{Gon} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.029		μs
			$T_{vj} = 125\ ^\circ C$		0.030		
			$T_{vj} = 150\ ^\circ C$		0.031		
Rise time (inductive load)	t_r	$I_C = 50\ A, V_{CE} = 300\ V, V_{GE} = \pm 15\ V, R_{Gon} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.059		μs
			$T_{vj} = 125\ ^\circ C$		0.060		
			$T_{vj} = 150\ ^\circ C$		0.061		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 50\ A, V_{CE} = 300\ V, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.180		μs
			$T_{vj} = 125\ ^\circ C$		0.210		
			$T_{vj} = 150\ ^\circ C$		0.220		
Fall time (inductive load)	t_f	$I_C = 50\ A, V_{CE} = 300\ V, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.110		μs
			$T_{vj} = 125\ ^\circ C$		0.140		
			$T_{vj} = 150\ ^\circ C$		0.150		
Turn-on energy loss per pulse	E_{on}	$I_C = 50\ A, V_{CE} = 300\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 8.2\ \Omega, di/dt = 550\ A/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		1.37		mJ
			$T_{vj} = 125\ ^\circ C$		1.78		
			$T_{vj} = 150\ ^\circ C$		1.89		
Turn-off energy loss per pulse	E_{off}	$I_C = 50\ A, V_{CE} = 300\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 8.2\ \Omega, dv/dt = 4000\ V/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		1.17		mJ
			$T_{vj} = 125\ ^\circ C$		1.57		
			$T_{vj} = 150\ ^\circ C$		1.66		
SC data	I_{SC}	$V_{GE} \leq 15\ V, V_{CC} = 360\ V, V_{CEmax} = V_{CES} - L_{sCE} \cdot di/dt$	$t_p \leq 6\ \mu s, T_{vj} = 150\ ^\circ C$		250		A
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT			1.02		K/W

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Temperature under switching conditions	$T_{vj\ op}$		-40		150	°C

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\ ^\circ\text{C}$	650	V
Continuous DC forward current	I_F		50	A
Repetitive peak forward current	I_{FRM}	$t_P = 1\ \text{ms}$	100	A
I^2t - value	I^2t	$V_R = 0\ \text{V}, t_P = 10\ \text{ms}$	$T_{vj} = 125\ ^\circ\text{C}$	A^2s
			$T_{vj} = 150\ ^\circ\text{C}$	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 50\ \text{A}, V_{GE} = 0\ \text{V}$	$T_{vj} = 25\ ^\circ\text{C}$	1.56	1.95	V
			$T_{vj} = 125\ ^\circ\text{C}$	1.49		
			$T_{vj} = 150\ ^\circ\text{C}$	1.45		
Peak reverse recovery current	I_{RM}	$I_F = 50\ \text{A}, V_R = 300\ \text{V}, V_{GE} = -15\ \text{V}, -di_F/dt = 550\ \text{A}/\mu\text{s} (T_{vj} = 150\ ^\circ\text{C})$	$T_{vj} = 25\ ^\circ\text{C}$	34		A
			$T_{vj} = 125\ ^\circ\text{C}$	48		
			$T_{vj} = 150\ ^\circ\text{C}$	53		
Recovered charge	Q_r	$I_F = 50\ \text{A}, V_R = 300\ \text{V}, V_{GE} = -15\ \text{V}, -di_F/dt = 550\ \text{A}/\mu\text{s} (T_{vj} = 150\ ^\circ\text{C})$	$T_{vj} = 25\ ^\circ\text{C}$	2.4		μC
			$T_{vj} = 125\ ^\circ\text{C}$	4.4		
			$T_{vj} = 150\ ^\circ\text{C}$	5.1		
Reverse recovery energy	E_{rec}	$I_F = 50\ \text{A}, V_R = 300\ \text{V}, V_{GE} = -15\ \text{V}, -di_F/dt = 550\ \text{A}/\mu\text{s} (T_{vj} = 150\ ^\circ\text{C})$	$T_{vj} = 25\ ^\circ\text{C}$	0.62		mJ
			$T_{vj} = 125\ ^\circ\text{C}$	1.11		
			$T_{vj} = 150\ ^\circ\text{C}$	1.28		
Thermal resistance, junction to heat sink	R_{thJH}	per diode		1.45		K/W
Temperature under switching conditions	$T_{vj\ op}$		-40		150	°C

4 Diode, Rectifier

Table 7 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25\text{ °C}$		1200	V
Maximum RMS forward current per chip	I_{FRMSM}	$T_H = 80\text{ °C}$		50	A
Maximum RMS current at rectifier output	I_{RMSM}	$T_H = 80\text{ °C}$		50	A
Surge forward current	I_{FSM}	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	493	A
			$T_{vj} = 150\text{ °C}$	378	
I^2t - value	I^2t	$t_p = 10\text{ ms}$	$T_{vj} = 25\text{ °C}$	1210	A ² s
			$T_{vj} = 150\text{ °C}$	714	

Table 8 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 50\text{ A}$	$T_{vj} = 150\text{ °C}$		0.98		V
Reverse current	I_r	$T_{vj} = 150\text{ °C}$, $V_R = 1200\text{ V}$			0.1		mA
Thermal resistance, junction to heat sink	R_{thJH}	per diode			1.43		K/W
Temperature under switching conditions	$T_{vj, op}$			-40		150	°C

5 IGBT, Boost

Table 9 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CES}		$T_{vj} = 25\text{ °C}$	650	V
Implemented collector current	I_{CN}			75	A
Continuous DC collector current	I_{CDC}	$T_{vj\text{ max}} = 175\text{ °C}$	$T_H = 80\text{ °C}$	40	A
Repetitive peak collector current	I_{CRM}	$t_p = 1\text{ ms}$		150	A
Gate-emitter peak voltage	V_{GES}			±20	V

Table 10 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 40\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		1.28	1.66	V
			$T_{vj} = 125\ ^\circ C$		1.35		
			$T_{vj} = 150\ ^\circ C$		1.37		
Gate threshold voltage	V_{GEth}	$I_C = 0.75\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$		3.85	4.60	5.35	V
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 400\ V$			0.326		μC
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$			0		Ω
Input capacitance	C_{ies}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			4.11		nF
Reverse transfer capacitance	C_{res}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$			0.014		nF
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 650\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			0.021	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				100	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 40\ A, V_{CE} = 300\ V, V_{GE} = \pm 15\ V, R_{Gon} = 6.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.026		μs
			$T_{vj} = 125\ ^\circ C$		0.028		
			$T_{vj} = 150\ ^\circ C$		0.029		
Rise time (inductive load)	t_r	$I_C = 40\ A, V_{CE} = 300\ V, V_{GE} = \pm 15\ V, R_{Gon} = 6.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.020		μs
			$T_{vj} = 125\ ^\circ C$		0.021		
			$T_{vj} = 150\ ^\circ C$		0.021		
Turn-off delay time (inductive load)	t_{doff}	$I_C = 40\ A, V_{CE} = 300\ V, V_{GE} = \pm 15\ V, R_{Goff} = 6.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.108		μs
			$T_{vj} = 125\ ^\circ C$		0.130		
			$T_{vj} = 150\ ^\circ C$		0.135		
Fall time (inductive load)	t_f	$I_C = 40\ A, V_{CE} = 300\ V, V_{GE} = \pm 15\ V, R_{Goff} = 6.2\ \Omega$	$T_{vj} = 25\ ^\circ C$		0.007		μs
			$T_{vj} = 125\ ^\circ C$		0.011		
			$T_{vj} = 150\ ^\circ C$		0.013		
Turn-on energy loss per pulse	E_{on}	$I_C = 40\ A, V_{CE} = 300\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 6.2\ \Omega, di/dt = 1150\ A/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		0.82		mJ
			$T_{vj} = 125\ ^\circ C$		1.2		
			$T_{vj} = 150\ ^\circ C$		1.28		
Turn-off energy loss per pulse	E_{off}	$I_C = 40\ A, V_{CE} = 300\ V, L_\sigma = 35\ nH, V_{GE} = \pm 15\ V, R_{Goff} = 6.2\ \Omega, dv/dt = 6500\ V/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$		0.26		mJ
			$T_{vj} = 125\ ^\circ C$		0.36		
			$T_{vj} = 150\ ^\circ C$		0.39		
Thermal resistance, junction to heat sink	R_{thJH}	per IGBT			1.40		K/W
Temperature under switching conditions	$T_{vj\ op}$			-40		150	$^\circ C$

6 Diode, Boost

Table 11 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ °C}$	650	V
Implemented forward current	I_{FN}			75	A
Continuous DC forward current	I_F			40	A
Repetitive peak forward current	I_{FRM}	$t_P = 1\text{ ms}$		150	A
I^2t - value	I^2t	$V_R = 0\text{ V}, t_P = 10\text{ ms}$	$T_{vj} = 125\text{ °C}$	320	A^2s
			$T_{vj} = 150\text{ °C}$	280	

Table 12 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 40\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$		1.28	V
			$T_{vj} = 125\text{ °C}$		1.20	
			$T_{vj} = 150\text{ °C}$		1.16	
Peak reverse recovery current	I_{RM}	$I_F = 40\text{ A}, V_R = 300\text{ V}, V_{GE} = -15\text{ V}, -di_F/dt = 1150\text{ A}/\mu s (T_{vj} = 150\text{ °C})$	$T_{vj} = 25\text{ °C}$		25.6	A
			$T_{vj} = 125\text{ °C}$		33.3	
			$T_{vj} = 150\text{ °C}$		36.4	
Recovered charge	Q_r	$I_F = 40\text{ A}, V_R = 300\text{ V}, V_{GE} = -15\text{ V}, -di_F/dt = 1150\text{ A}/\mu s (T_{vj} = 150\text{ °C})$	$T_{vj} = 25\text{ °C}$		1.25	μC
			$T_{vj} = 125\text{ °C}$		2.62	
			$T_{vj} = 150\text{ °C}$		3.04	
Reverse recovery energy	E_{rec}	$I_F = 40\text{ A}, V_R = 300\text{ V}, V_{GE} = -15\text{ V}, -di_F/dt = 1150\text{ A}/\mu s (T_{vj} = 150\text{ °C})$	$T_{vj} = 25\text{ °C}$		0.2	mJ
			$T_{vj} = 125\text{ °C}$		0.43	
			$T_{vj} = 150\text{ °C}$		0.52	
Thermal resistance, junction to heat sink	R_{thJH}	per diode		1.52		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		150	°C

7 Diode, Reverse

Table 13 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = 25\text{ °C}$	650	V
Continuous DC forward current	I_F			10	A
Repetitive peak forward current	I_{FRM}	$t_P = 1\text{ ms}$		20	A
I^2t - value	I^2t	$V_R = 0\text{ V}, t_P = 10\text{ ms}$	$T_{vj} = 125\text{ °C}$	12.5	A^2s
			$T_{vj} = 150\text{ °C}$	9.5	

Table 14 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Forward voltage	V_F	$I_F = 10\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ °C}$	1.60	2.00	V
			$T_{vj} = 125\text{ °C}$	1.55		
			$T_{vj} = 150\text{ °C}$	1.52		
Thermal resistance, junction to heat sink	R_{thJH}	per diode		3.92		K/W
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		150	°C

8 NTC-Thermistor

Table 15 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rated resistance	R_{25}	$T_{NTC} = 25\text{ °C}$		5		kΩ
Deviation of R_{100}	$\Delta R/R$	$T_{NTC} = 100\text{ °C}, R_{100} = 493\text{ Ω}$	-5		5	%
Power dissipation	P_{25}	$T_{NTC} = 25\text{ °C}$			20	mW
B-value	$B_{25/50}$	$R_2 = R_{25} \exp[B_{25/50}(1/T_2 - 1/(298,15\text{ K}))]$		3375		K
B-value	$B_{25/80}$	$R_2 = R_{25} \exp[B_{25/80}(1/T_2 - 1/(298,15\text{ K}))]$		3411		K
B-value	$B_{25/100}$	$R_2 = R_{25} \exp[B_{25/100}(1/T_2 - 1/(298,15\text{ K}))]$		3433		K

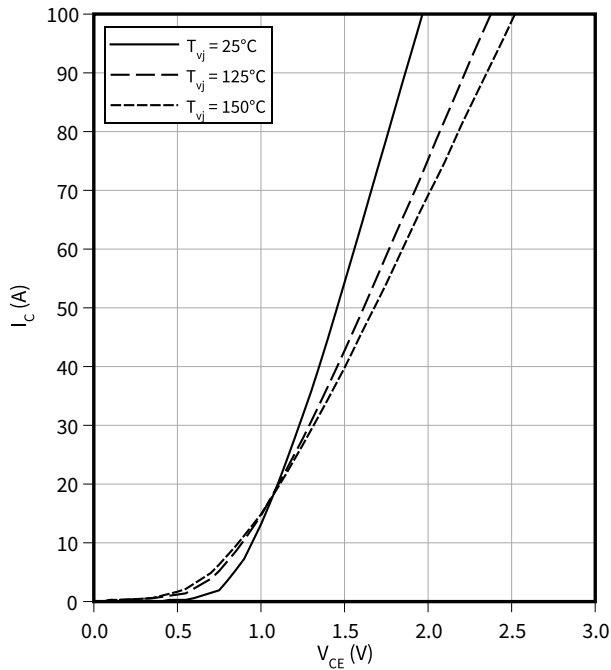
Note: Specification according to the valid application note.

9 Characteristics diagrams

Output characteristic (typical), IGBT, Inverter

$I_C = f(V_{CE})$

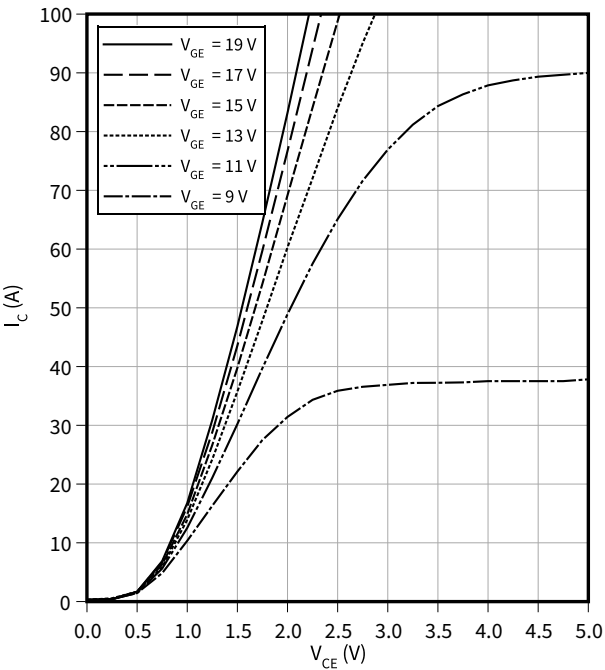
$V_{GE} = 15\text{ V}$



Output characteristic field (typical), IGBT, Inverter

$I_C = f(V_{CE})$

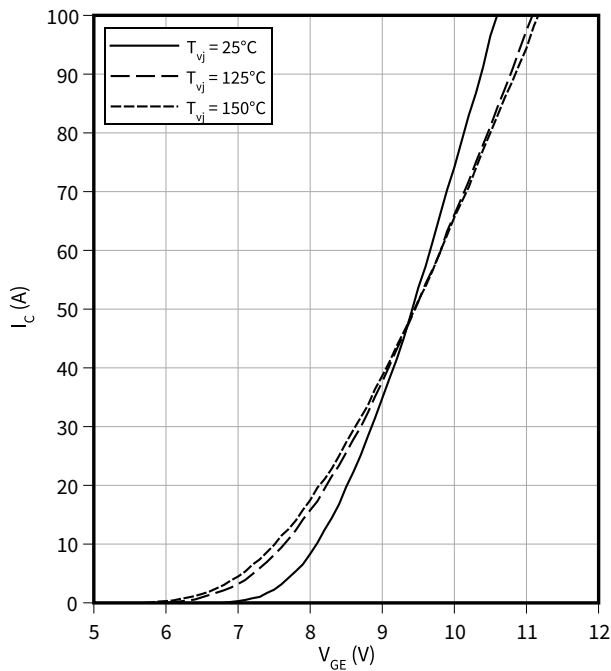
$T_{vj} = 150\text{ °C}$



Transfer characteristic (typical), IGBT, Inverter

$I_C = f(V_{GE})$

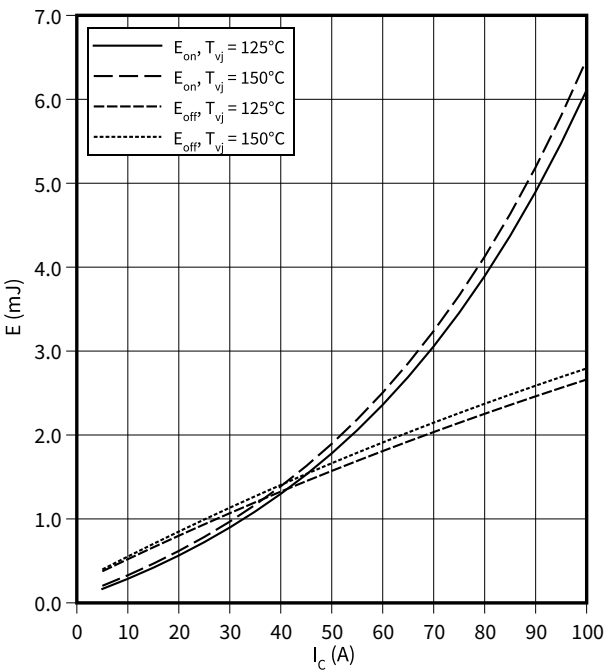
$V_{CE} = 20\text{ V}$



Switching losses (typical), IGBT, Inverter

$E = f(I_C)$

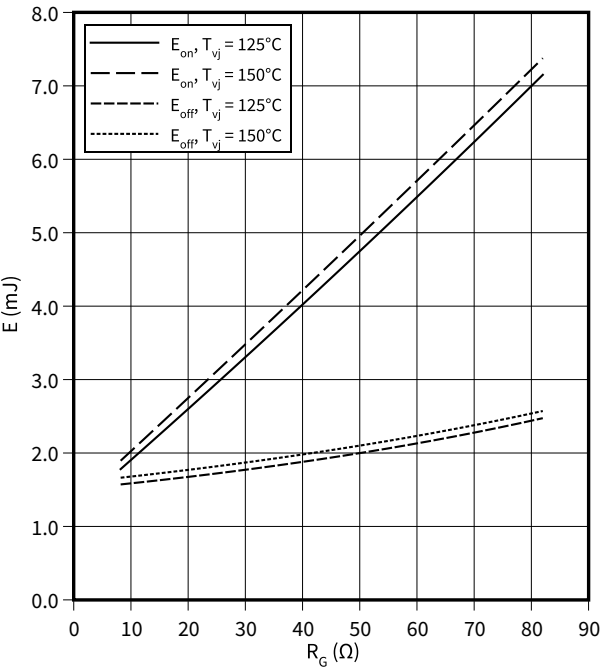
$R_{Goff} = 8.2\text{ }\Omega$, $R_{Gon} = 8.2\text{ }\Omega$, $V_{CE} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$



9 Characteristics diagrams

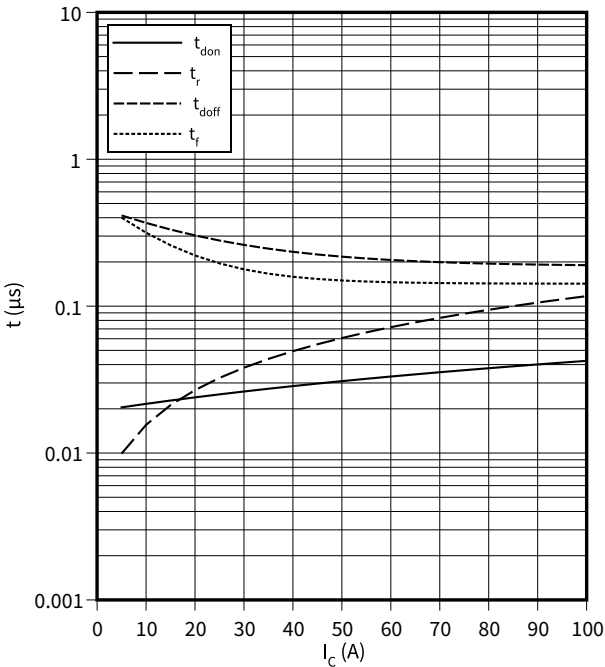
Switching losses (typical), IGBT, Inverter

$E = f(R_G)$
 $V_{GE} = \pm 15\text{ V}$, $I_C = 50\text{ A}$, $V_{CE} = 300\text{ V}$



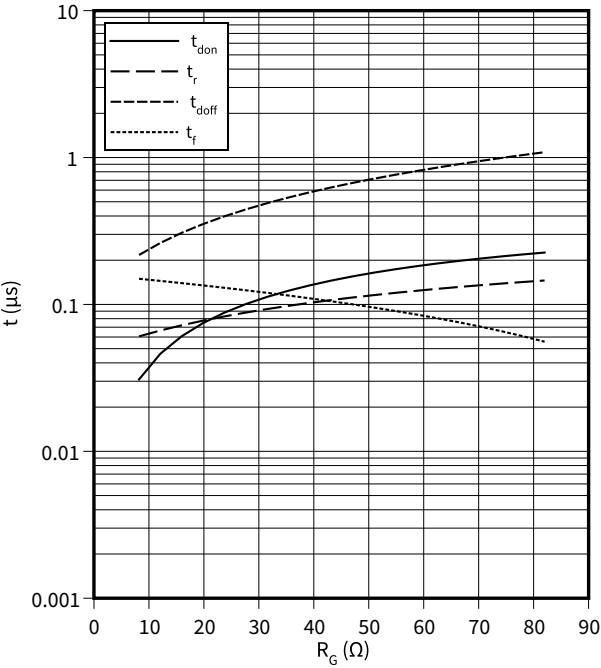
Switching times (typical), IGBT, Inverter

$t = f(I_C)$
 $R_{Goff} = 8.2\ \Omega$, $R_{Gon} = 8.2\ \Omega$, $V_{CE} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 150\text{ °C}$



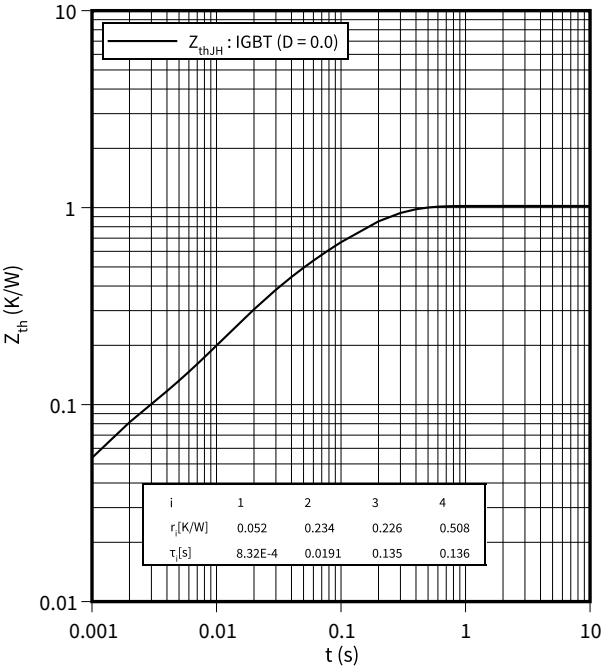
Switching times (typical), IGBT, Inverter

$t = f(R_G)$
 $I_C = 50\text{ A}$, $V_{CE} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 150\text{ °C}$



Transient thermal impedance , IGBT, Inverter

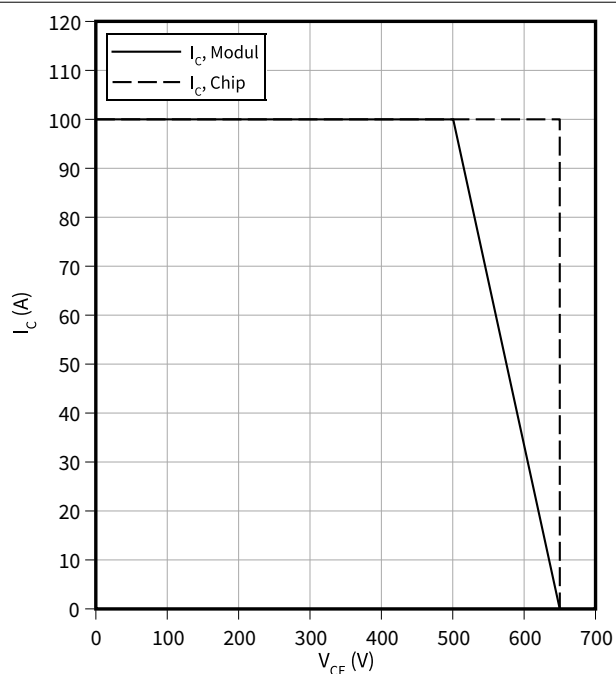
$Z_{th} = f(t)$



Reverse bias safe operating area (RBSOA), IGBT, Inverter

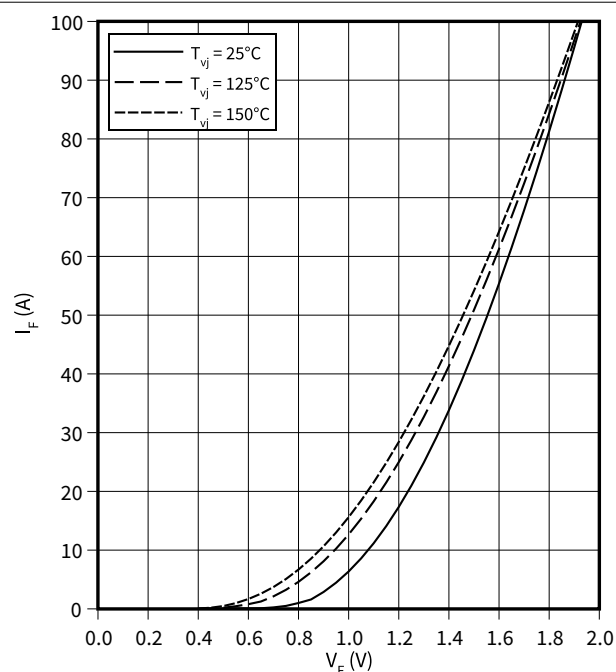
$$I_C = f(V_{CE})$$

$R_{Goff} = 8.2 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $T_{vj} = 150^\circ \text{C}$



Forward characteristic (typical), Diode, Inverter

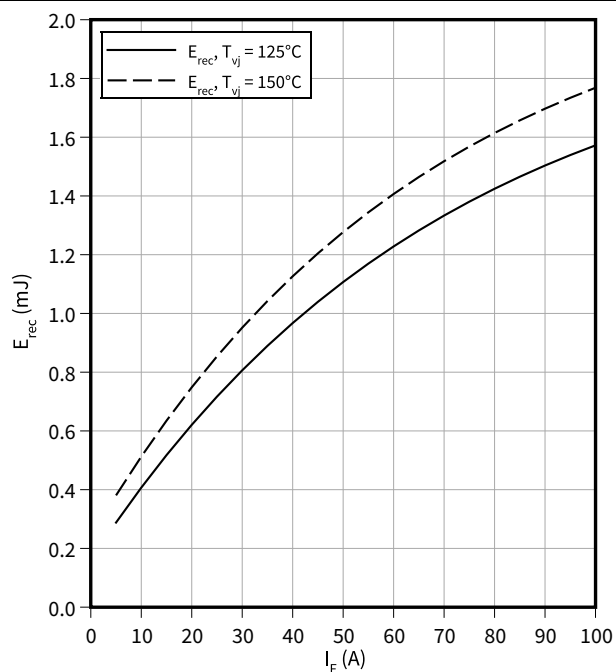
$$I_F = f(V_F)$$



Switching losses (typical), Diode, Inverter

$$E_{rec} = f(I_F)$$

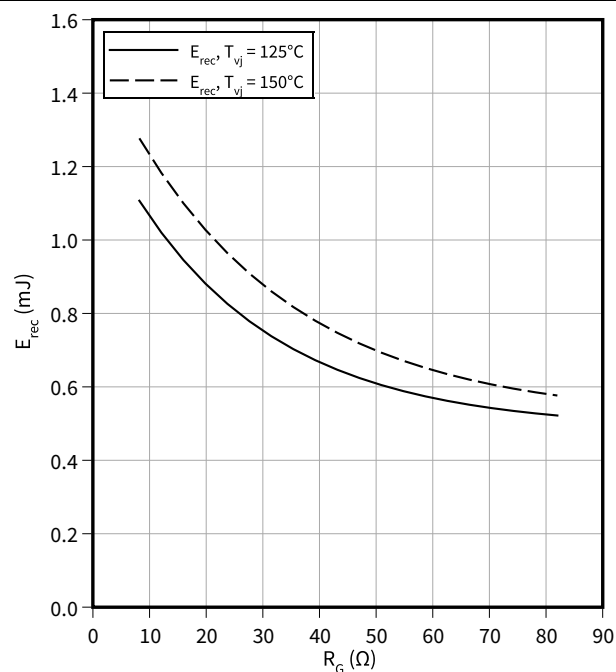
$V_{CE} = 300 \text{ V}$, $R_{Gon} = 8.2 \Omega$



Switching losses (typical), Diode, Inverter

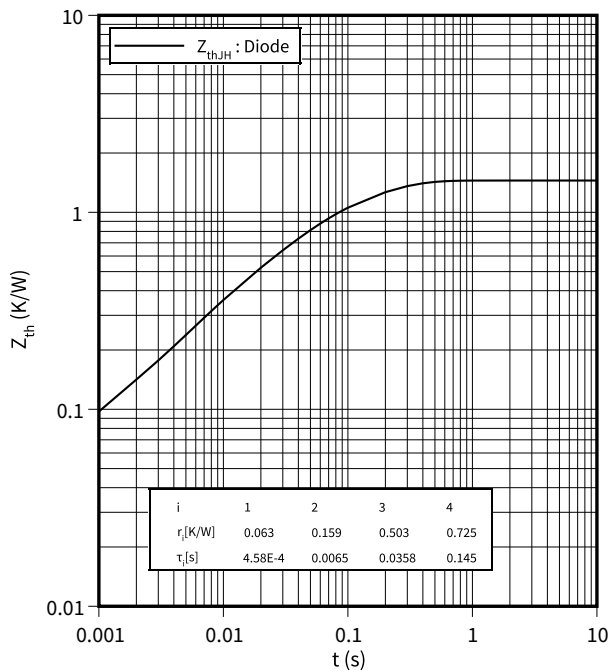
$$E_{rec} = f(R_G)$$

$V_{CE} = 300 \text{ V}$, $I_F = 50 \text{ A}$



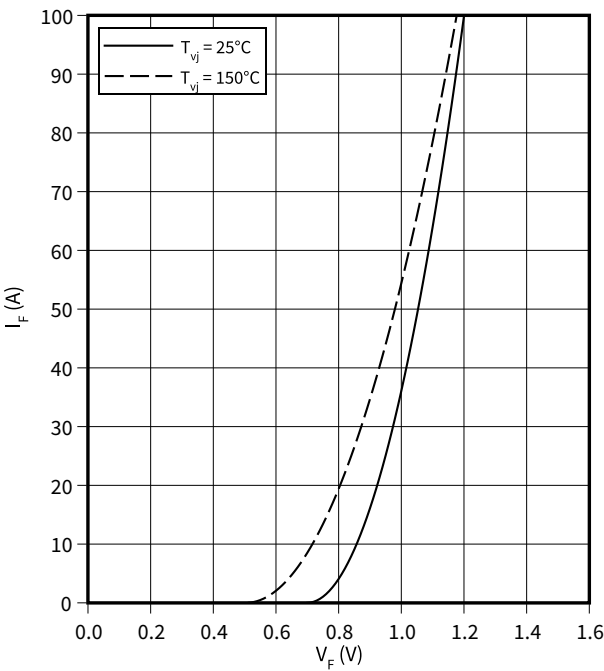
Transient thermal impedance, Diode, Inverter

$Z_{th} = f(t)$



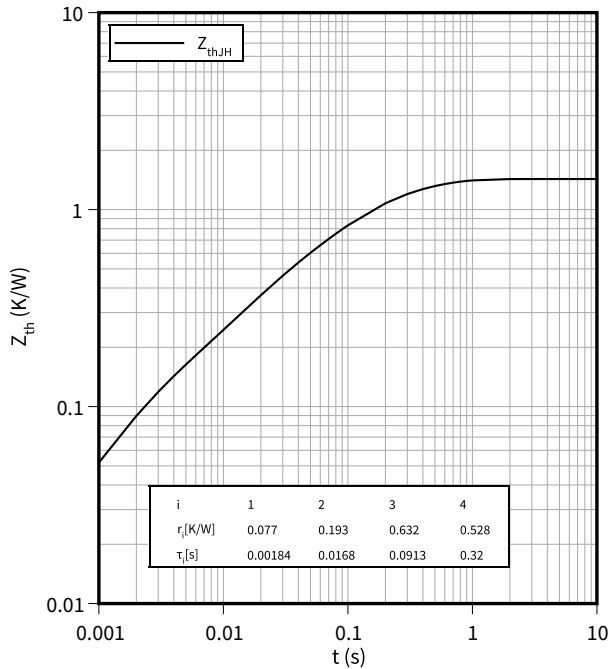
Forward characteristic (typical), Diode, Rectifier

$I_F = f(V_F)$



Transient thermal impedance, Diode, Rectifier

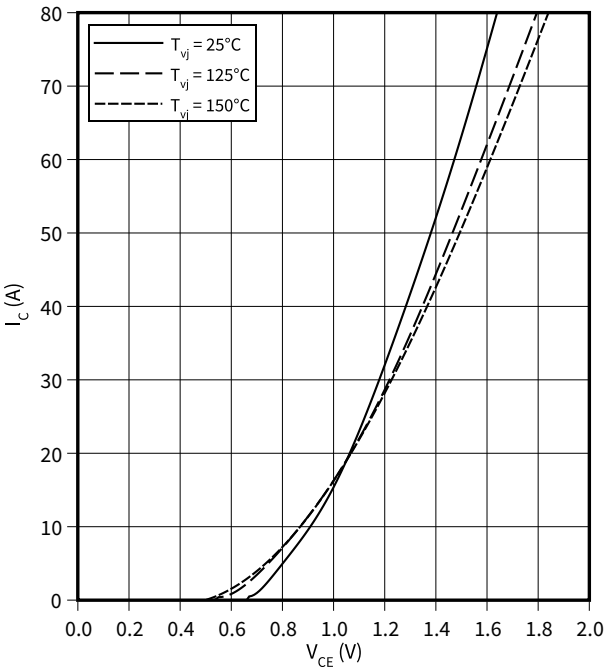
$Z_{th} = f(t)$



Output characteristic (typical), IGBT, Boost

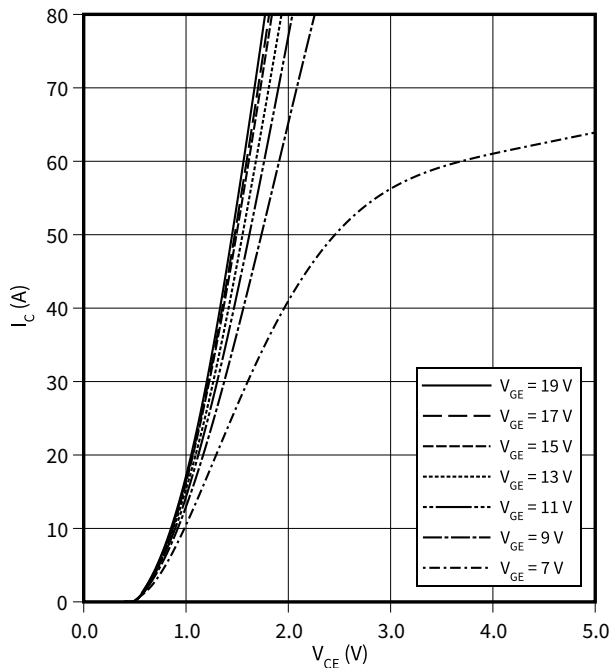
$I_C = f(V_{CE})$

$V_{GE} = 15\text{ V}$



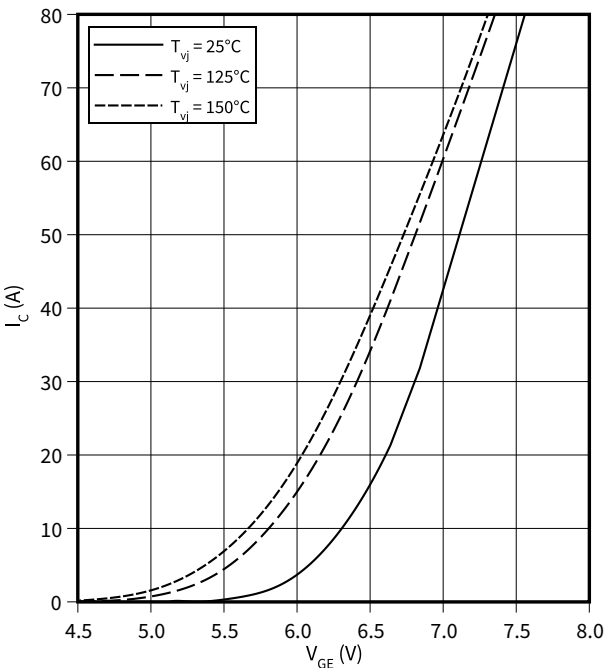
Output characteristic field (typical), IGBT, Boost

$I_C = f(V_{CE})$
 $T_{vj} = 150\text{ }^{\circ}\text{C}$



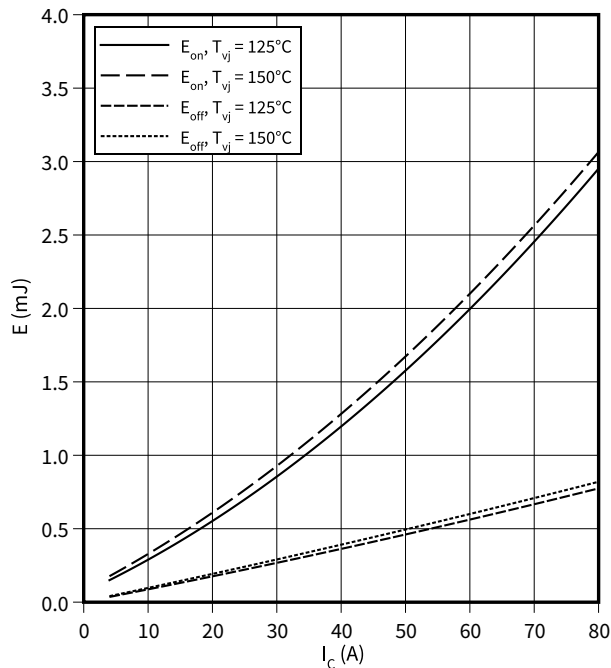
Transfer characteristic (typical), IGBT, Boost

$I_C = f(V_{GE})$
 $V_{CE} = 20\text{ V}$



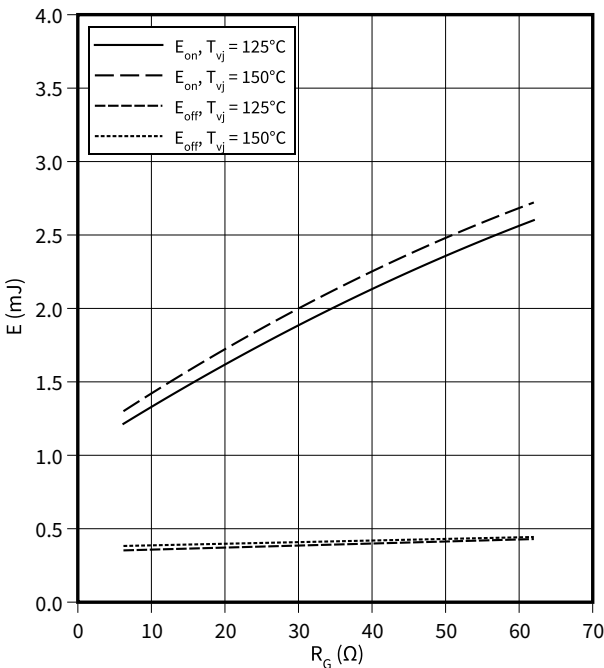
Switching losses (typical), IGBT, Boost

$E = f(I_C)$
 $R_{Goff} = 6.2\text{ }\Omega$, $R_{Gon} = 6.2\text{ }\Omega$, $V_{CE} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$



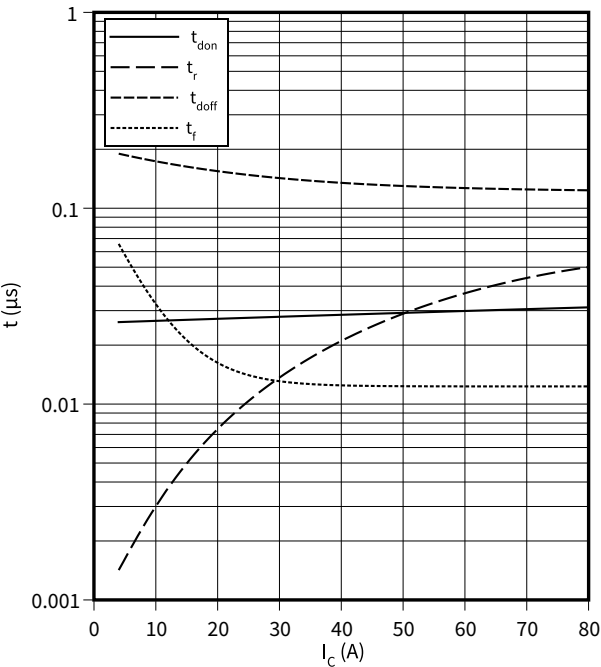
Switching losses (typical), IGBT, Boost

$E = f(R_G)$
 $I_C = 40\text{ A}$, $V_{CE} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$



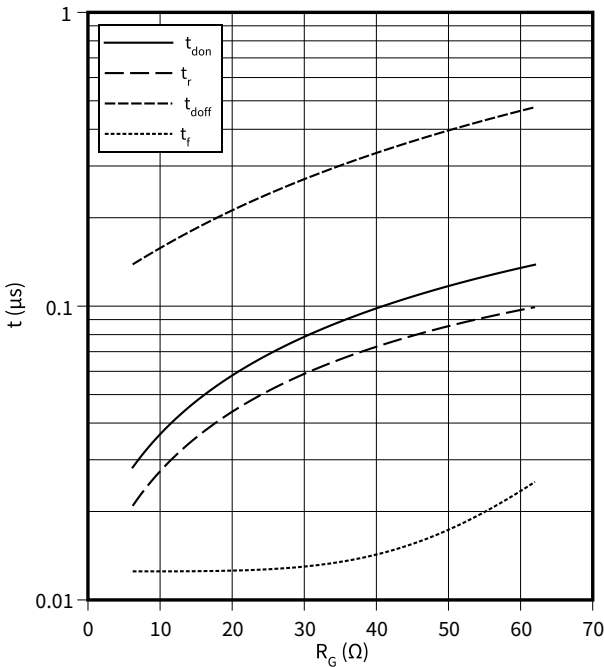
Switching times (typical), IGBT, Boost

$t = f(I_C)$
 $R_{Goff} = 6.2\ \Omega$, $R_{Gon} = 6.2\ \Omega$, $V_{CE} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 150\text{ }^\circ\text{C}$



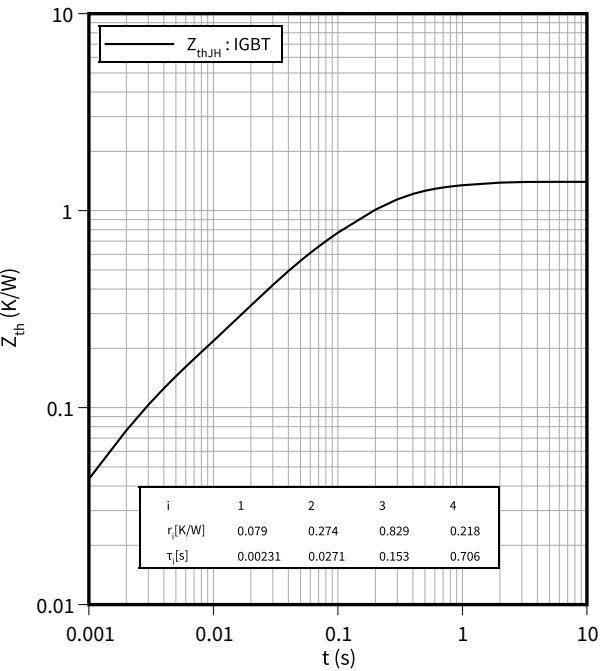
Switching times (typical), IGBT, Boost

$t = f(R_G)$
 $I_C = 40\text{ A}$, $V_{CE} = 300\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 150\text{ }^\circ\text{C}$



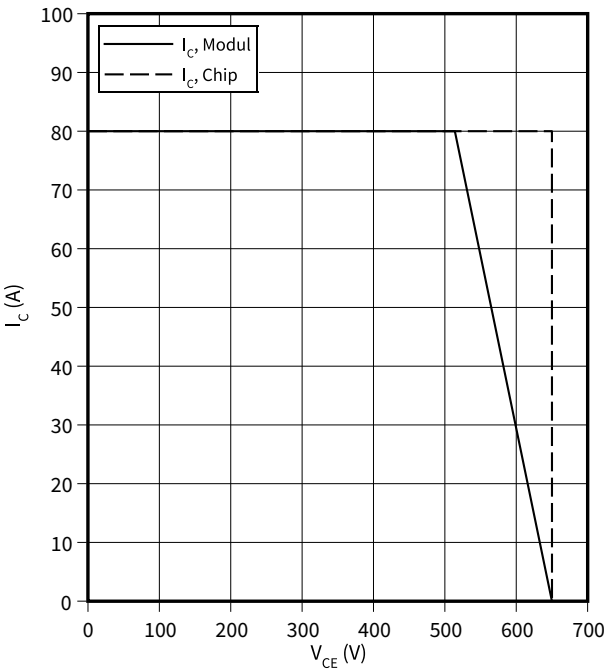
Transient thermal impedance , IGBT, Boost

$Z_{th} = f(t)$



Reverse bias safe operating area (RBSOA), IGBT, Boost

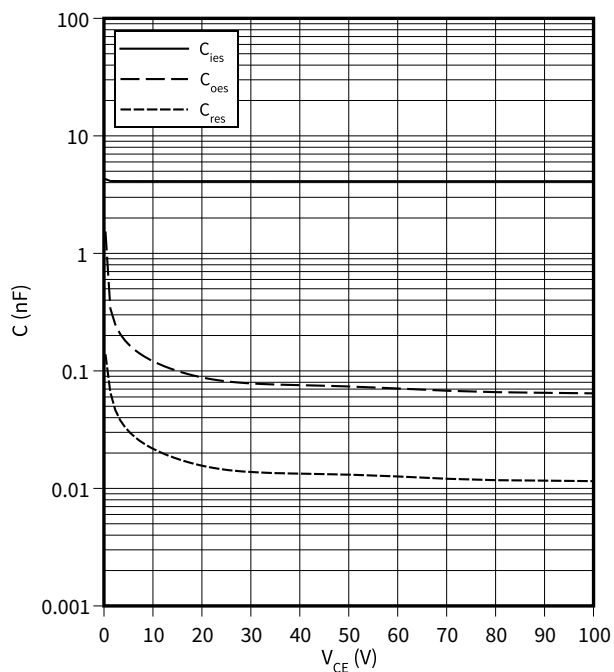
$I_C = f(V_{CE})$
 $R_{Goff} = 6.2\ \Omega$, $V_{GE} = \pm 15\text{ V}$, $T_{vj} = 150\text{ }^\circ\text{C}$



Capacity characteristic (typical), IGBT, Boost

$$C = f(V_{CE})$$

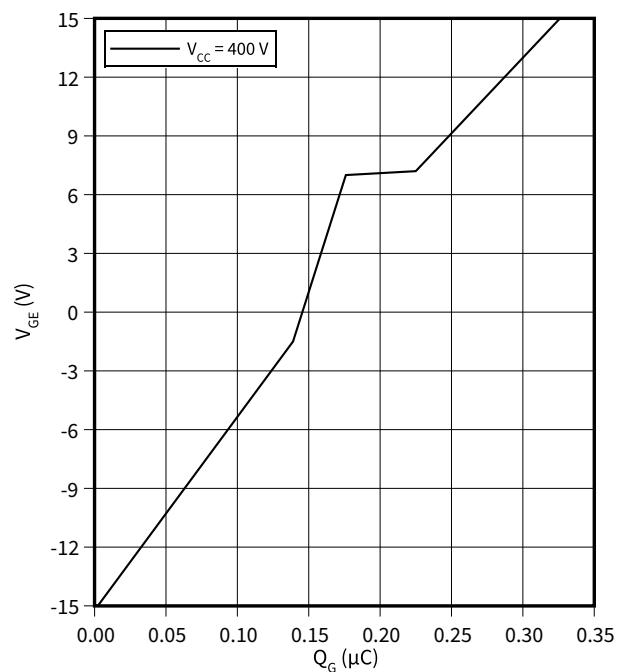
$f = 1000 \text{ kHz}$, $V_{GE} = 0 \text{ V}$, $T_{vj} = 25 \text{ °C}$



Gate charge characteristic (typical), IGBT, Boost

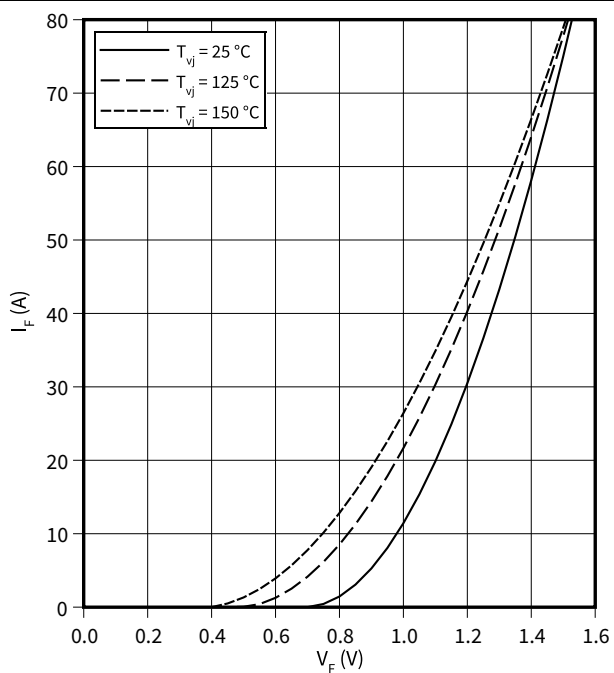
$$V_{GE} = f(Q_G)$$

$I_C = 75 \text{ A}$, $T_{vj} = 25 \text{ °C}$



Forward characteristic (typical), Diode, Boost

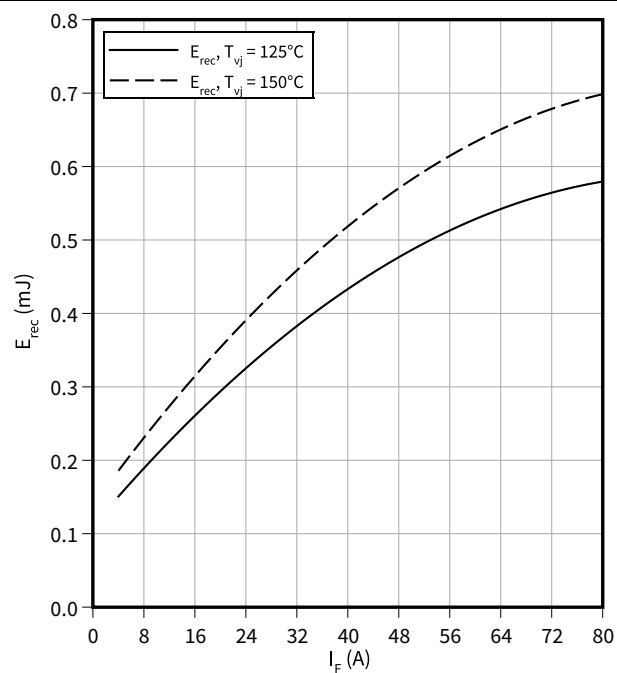
$$I_F = f(V_F)$$



Switching losses (typical), Diode, Boost

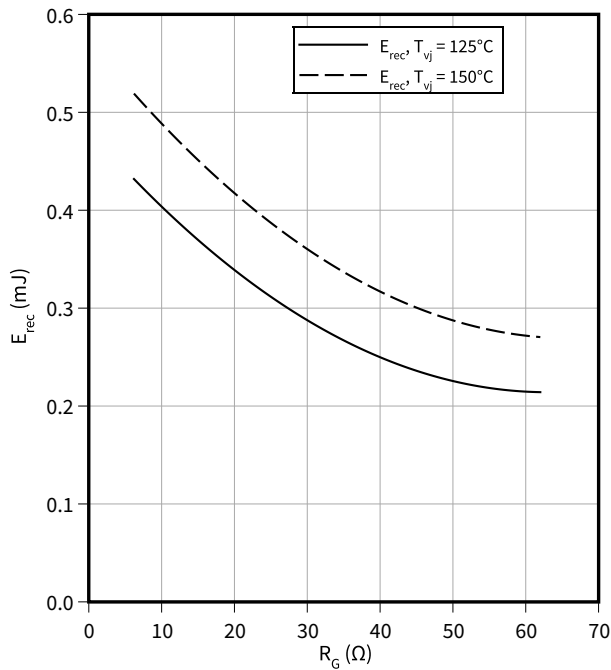
$$E_{rec} = f(I_F)$$

$V_{CE} = 300 \text{ V}$, $R_{Gon} = 6.2 \Omega$



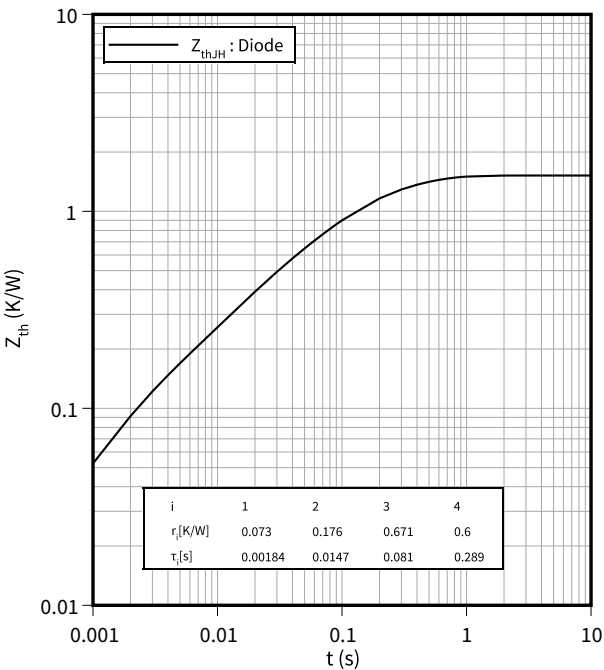
Switching losses (typical), Diode, Boost

$E_{rec} = f(R_G)$
 $V_{CE} = 300\text{ V}, I_F = 50\text{ A}$



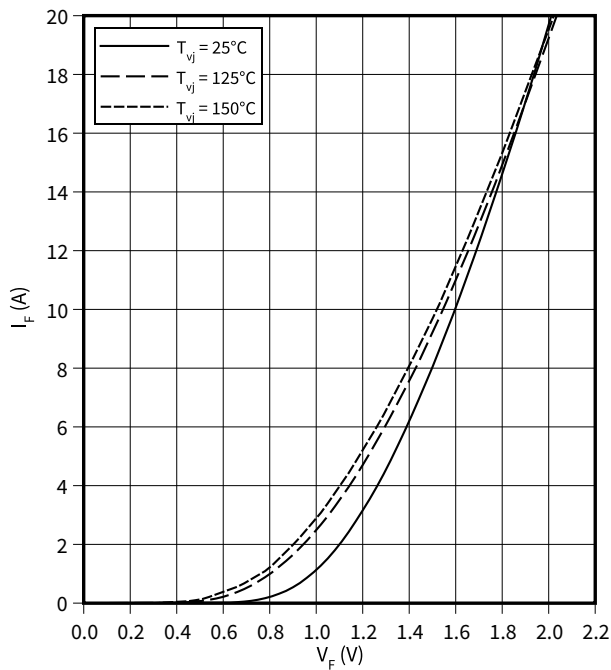
Transient thermal impedance, Diode, Boost

$Z_{th} = f(t)$



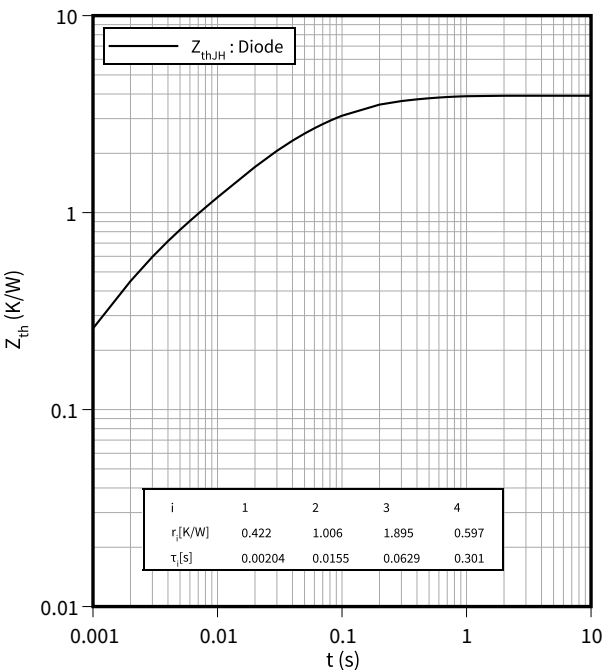
Forward characteristic (typical), Diode, Reverse

$I_F = f(V_F)$



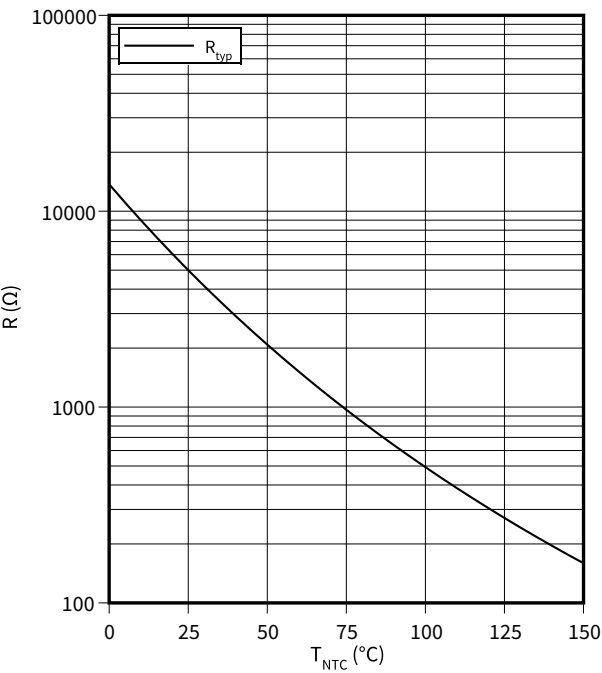
Transient thermal impedance, Diode, Reverse

$Z_{th} = f(t)$



Temperature characteristic (typical), NTC-Thermistor

$R = f(T_{NTC})$



10 Circuit diagram

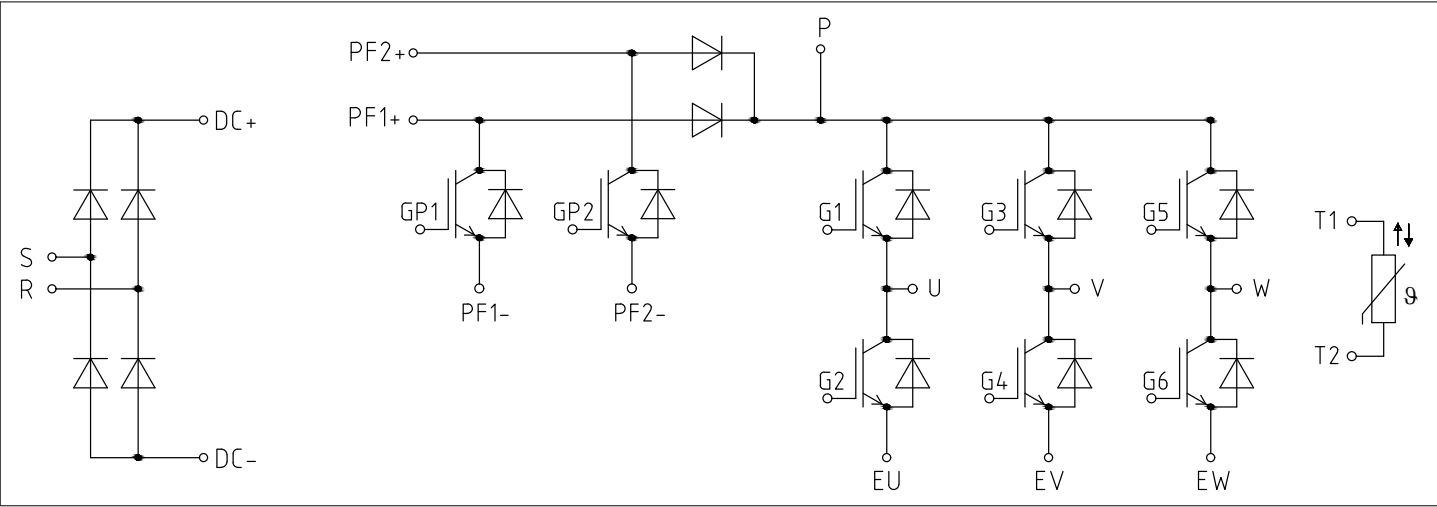


Figure 1

11 Package outlines

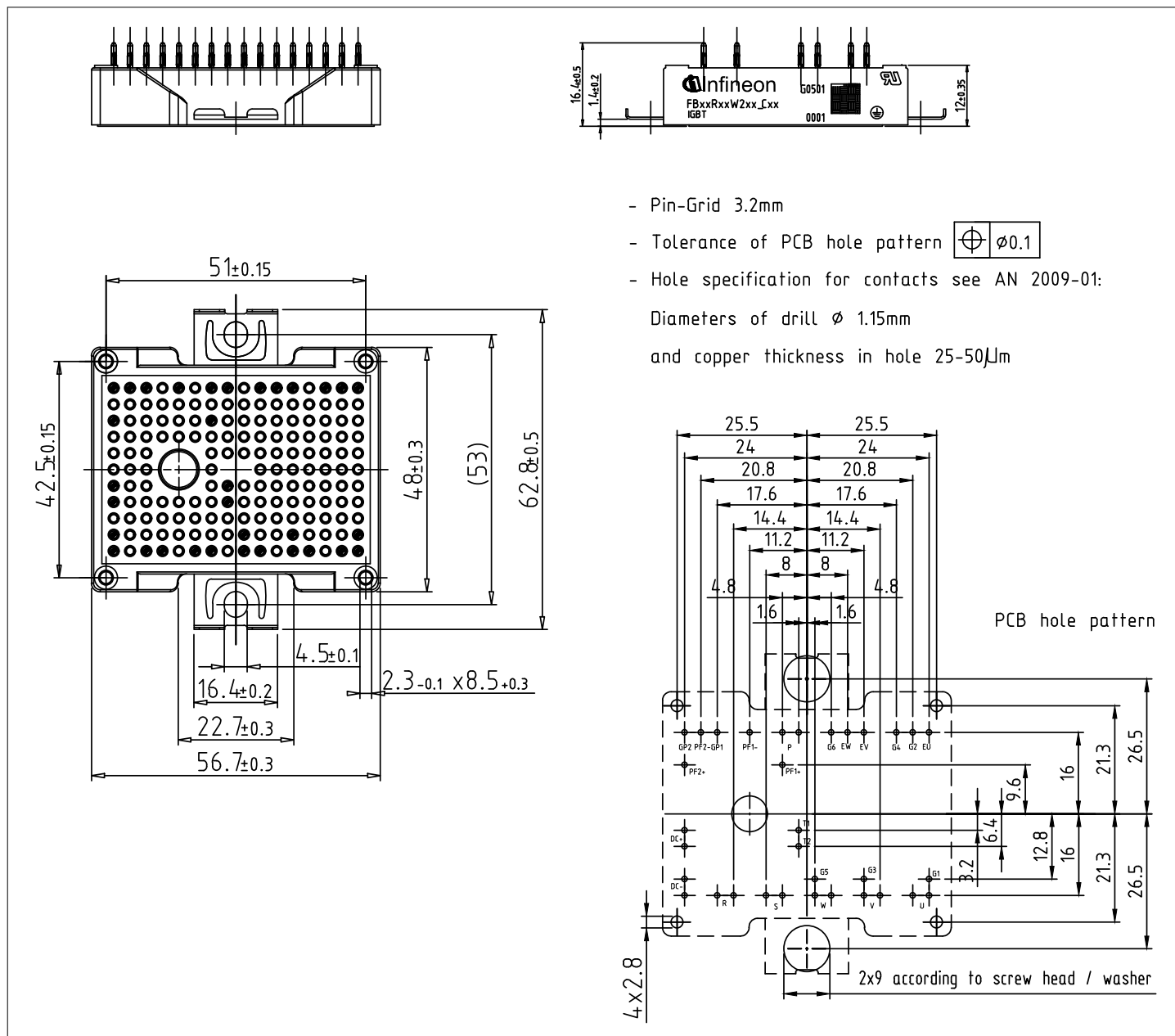


Figure 2

12 Module label code

Module label code			
Code format	Data Matrix		Barcode Code128
Encoding	ASCII text		Code Set A
Symbol size	16x16		23 digits
Standard	IEC24720 and IEC16022		IEC8859-1
Code content	<i>Content</i>	<i>Digit</i>	<i>Example</i>
	Module serial number	1 – 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 – 21	15
	Date code (production week)	22 – 23	30
Example			
			
71549142846550549911530		71549142846550549911530	

Figure 3

Revision history

Document version	Date of release	Description of changes
0.10	2021-07-29	Initial version
1.00	2021-12-03	Final datasheet
1.10	2022-01-19	Final datasheet updated to V1.10

Trademarks

All referenced product or service names and trademarks are the property of their respective owners.

Edition 2022-01-19

Published by

Infineon Technologies AG
81726 Munich, Germany

© 2022 Infineon Technologies AG
All Rights Reserved.

Do you have a question about any aspect of this document?

Email: erratum@infineon.com

Document reference
IFX-ABB297-003

IMPORTANT NOTICE

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics ("Beschaffenhheitsgarantie").

With respect to any examples, hints or any typical values stated herein and/or any information regarding the application of the product, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation warranties of non-infringement of intellectual property rights of any third party.

In addition, any information given in this document is subject to customer's compliance with its obligations stated in this document and any applicable legal requirements, norms and standards concerning customer's products and any use of the product of Infineon Technologies in customer's applications.

The data contained in this document is exclusively intended for technically trained staff. It is the responsibility of customer's technical departments to evaluate the suitability of the product for the intended application and the completeness of the product information given in this document with respect to such application.

WARNINGS

Due to technical requirements products may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies office.

Except as otherwise explicitly approved by Infineon Technologies in a written document signed by authorized representatives of Infineon Technologies, Infineon Technologies' products may not be used in any applications where a failure of the product or any consequences of the use thereof can reasonably be expected to result in personal injury.